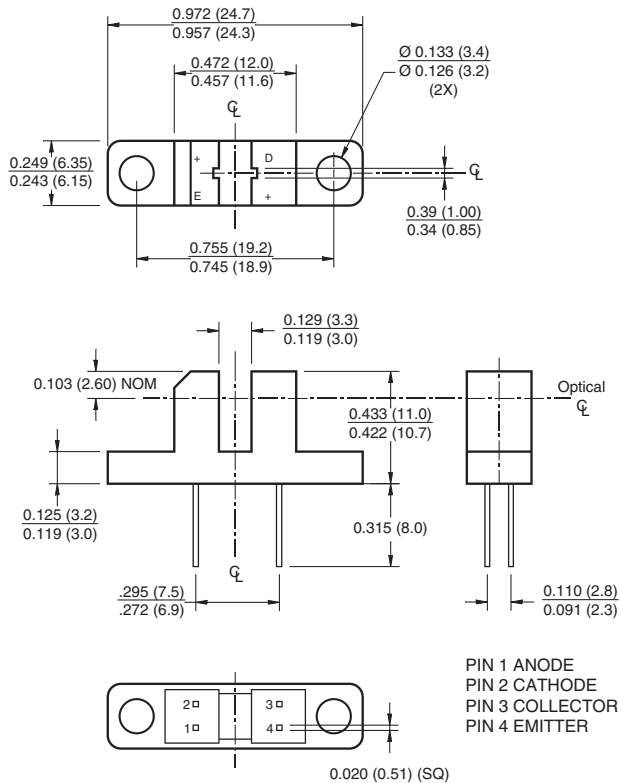


H21B1

H21B2

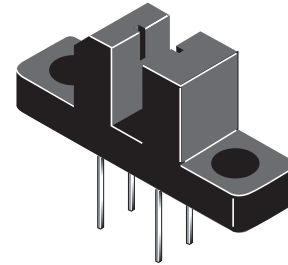
H21B3

PACKAGE DIMENSIONS

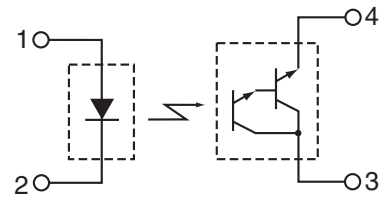


NOTES:

1. Dimensions for all drawings are in inches (mm).
2. Tolerance of $\pm .010$ (.25) on all non-nominal dimensions unless otherwise specified.



SCHEMATIC



DESCRIPTION

The H21B1, H21B2 and H21B3 consist of a gallium arsenide infrared emitting diode coupled with a silicon photodarlington in a plastic housing. The packaging system is designed to optimize the mechanical resolution, coupling efficiency, ambient light rejection, cost and reliability. The gap in the housing provides a means of interrupting the signal with an opaque material, switching the output from an "ON" to an "OFF" state.

FEATURES

- Opaque housing
- Low cost
- .035" apertures
- High $I_{C(ON)}$

H21B1

H21B2

H21B3

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Rating	Unit
Operating Temperature	T_{OPR}	-55 to +100	$^\circ\text{C}$
Storage Temperature	T_{STG}	-55 to +100	$^\circ\text{C}$
Soldering Temperature (Iron) ^(2,3 and 4)	T_{SOL-I}	240 for 5 sec	$^\circ\text{C}$
Soldering Temperature (Flow) ^(2 and 3)	T_{SOL-F}	260 for 10 sec	$^\circ\text{C}$
INPUT (EMITTER)			
Continuous Forward Current	I_F	50	mA
Reverse Voltage	V_R	6	V
Power Dissipation ⁽¹⁾	P_D	100	mW
OUTPUT (SENSOR)			
Collector to Emitter Voltage	V_{CEO}	30	V
Emitter to Collector Voltage	V_{ECO}	6	V
Collector Current	I_C	40	mA
Power Dissipation ($T_C = 25^\circ\text{C}$) ⁽¹⁾	P_D	150	mW

NOTES:

1. Derate power dissipation linearly 1.67 mW/ $^\circ\text{C}$ above 25 $^\circ\text{C}$.
2. RMA flux is recommended.
3. Methanol or isopropyl alcohols are recommended as cleaning agents.
4. Soldering iron 1/16" (1.6 mm) minimum from housing.

H21B1

H21B2

H21B3

ELECTRICAL/OPTICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$)

PARAMETER	TEST CONDITIONS	SYMBOL	DEVICES	MIN	TYP	MAX	UNITS
INPUT (EMITTER)							
Forward Voltage	$I_F = 60 \text{ mA}$	V_F	All	—	—	1.7	V
Reverse Breakdown Voltage	$I_R = 10 \mu\text{A}$	V_R	All	6.0	—	—	V
Reverse Leakage Current	$V_R = 3 \text{ V}$	I_R	All	—	—	1.0	μA
OUTPUT (SENSOR)							
Emitter to Collector Breakdown	$I_F = 100 \mu\text{A}, E_e = 0$	BV_{ECO}	All	7.0	—	—	V
Collector to Emitter Breakdown	$I_C = 1 \text{ mA}, E_e = 0$	BV_{CEO}	All	30	—	—	V
Collector to Emitter Leakage	$V_{CE} = 25 \text{ V}, E_e = 0$	I_{CEO}	All	—	—	100	nA
COUPLED							
On-State Collector Current	$I_F = 2 \text{ mA}, V_{CE} = 1.5 \text{ V}$	$I_{C(ON)}$	H21B1	0.5	—	—	mA
			H21B2	1.0	—	—	
			H21B3	2.0	—	—	
	$I_F = 5 \text{ mA}, V_{CE} = 1.5 \text{ V}$		H21B1	2.5	—	—	
			H21B2	5.0	—	—	
			H21B3	10	—	—	
	$I_F = 10 \text{ mA}, V_{CE} = 1.5 \text{ V}$		H21B1	7.5	—	—	
			H21B2	14	—	—	
			H21B3	25	—	—	
Saturation Voltage	$I_F = 10 \text{ mA}, I_C = 1.8 \text{ mA}$	$V_{CE(SAT)}$	All	—	—	1.0	V
	$I_F = 60 \text{ mA}, I_C = 50 \text{ mA}$		H21B1/2	—	—	1.5	V
Turn-On Time	$I_F = 10 \text{ mA}, V_{CC} = 5 \text{ V}, R_L = 750\Omega$	t_{on}	All	—	45	—	μs
	$I_F = 60 \text{ mA}, V_{CC} = 5 \text{ V}, R_L = 75\Omega$		All	—	7	—	
Turn-Off Time	$I_F = 10 \text{ mA}, V_{CC} = 5 \text{ V}, R_L = 750\Omega$	t_{off}	All	—	250	—	μs
	$I_F = 60 \text{ mA}, V_{CC} = 5 \text{ V}, R_L = 75\Omega$		All	—	45	—	

H21B1

H21B2

H21B3

Figure 1. Output Current vs. Input Current

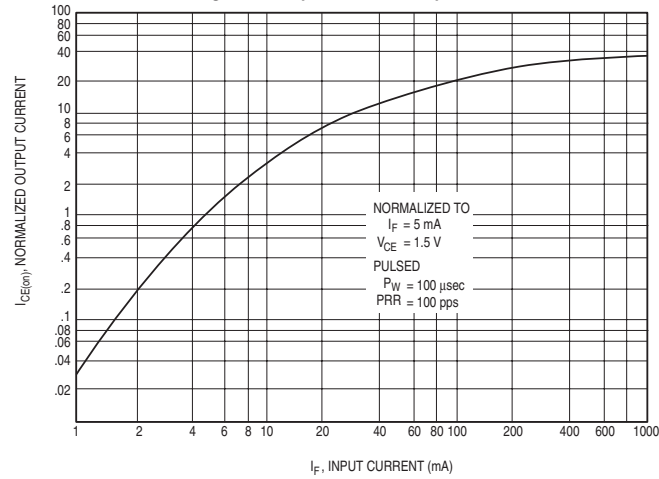


Figure 2. Output Current vs. Temperature

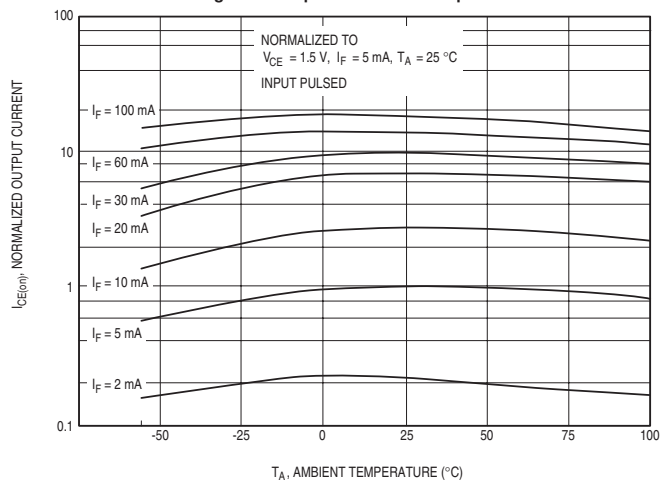
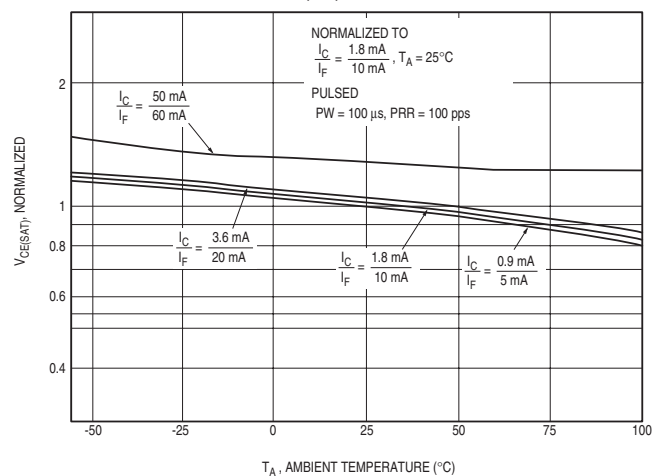


Figure 3. $V_{CE(SAT)}$ vs. Temperature



H21B1

H21B2

H21B3

Figure 4. Leakage Current vs. Temperature

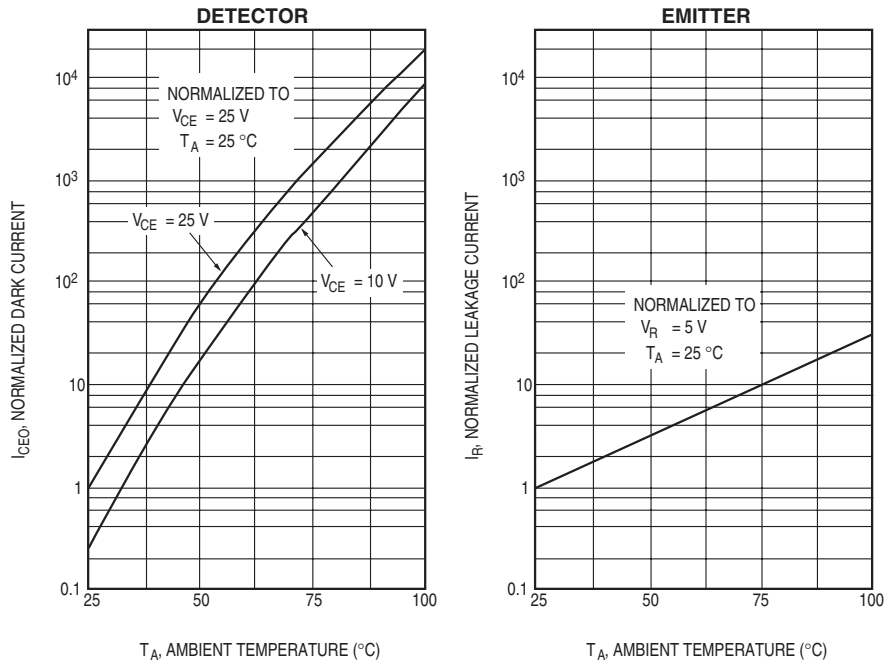


Figure 5. Switching Speed vs. R_L

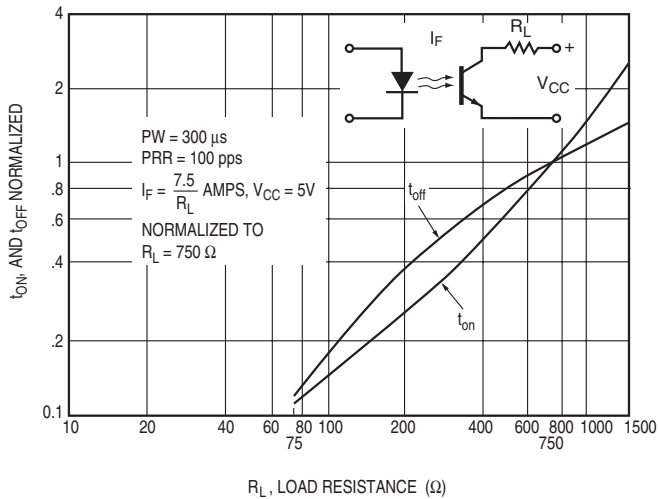
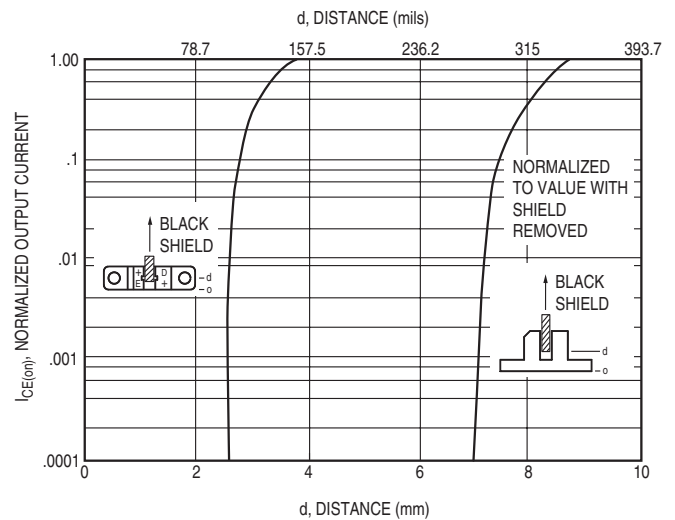


Figure 6. Output Current vs. Distance



H21B1

H21B2

H21B3

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